

Bridge Rectifier DF005S1-DF10S1

Description

With the ever-pressing need to improve power supply efficiency, improve surge rating, improve reliability, and reduce size, the DFxS1 family sets a new standard in performance and cost saving.

The DFxS1 family balances performance against cost. The design offers a moderate surge rating of 35 A required to handle inrush surge and maintain good reliability, with fair price.

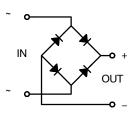
The DFxS1 achieves good performance in a SDIP surface mount form factor, reducing board space and volumetric requirements vs. competitive devices.

Features

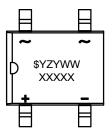
- Maximum Surge Rating:
 - $I_{FSM} = 35 A$
 - $I^2t = 5.1 A^2Sec$
- Optimized V_F: Typical 0.95 V at 1 A, 25°C
- DF10S Socket Compatible
- Glass Passivated Junctions
- Lead Free Compliant to EU RoHS 2002/95/EU Directives
- Green Molding Compound: IEC61249
- Qualified with IR Reflow and Wave Soldering



PDIP4 GW CASE 709AE



MARKING DIAGRAM



\$Y = onsemi Logo Z = Assemlby Plant Code YWW = Date Code (Year and Week)

XXXXX = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

1

DF005S1-DF10S1

ABSOLUTE MAXIMUM RATINGS (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

		Value							
Symbol	Parameter	DF005S1	DF01S1	DF02S1	DF04S1	DF06S1	DF08S1	DF10S1	Unit
V _{RRM}	Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
V _{RMS}	Maximum RMS Bridge Input Voltage	35	70	140	280	420	560	700	V
V_{DC}	Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
I _{F(AV)}	Maximum Average Forward Current T _A = 40°C		1.0					Α	
I _{FSM}	Peak Forward Surge Current 8.3 ms Single Half-Sine Wave Superimposed on Rated Load (JEDEC Method)		35			А			
T _{STG}	Storage Temperature Range	−55 to +150			°C				
TJ	Operating Junction Temperature Range	−55 to +150			°C				

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Max.	Unit
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient	Single-Die Measurement (Maximum Land Pattern: 13 × 13 mm)	65	°C/W
		Multi-Die Measurement (Maximum Land Pattern: 13 × 13 mm)	50	
		Multi-Die Measurement (Minimum Land Pattern: 1.3 × 1.5 mm)	105	
$\Psi_{\sf JL}$	Thermal Characterization Parameter, Junction to Lead	Single-Die Measurement (Maximum and Minimum Land Pattern)	27	°C/W

The thermal resistances (R_{θJA} & Ψ_{JL}) are characterized with the device mounted on the following FR4 printed circuit boards, as shown in Figure 1 and Figure 2. PCB size: 76.2 × 114.3 mm.
 Heating effect from adjacent dice is considered and only two dices are powered at the same time.

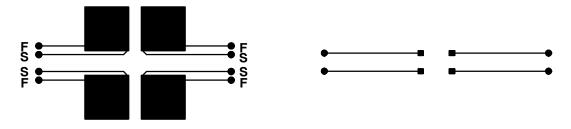


Figure 1. Maximum Pads of 2 oz Copper

Figure 2. Minimum Pads of 2 oz Copper

ELECTRICAL CHARACTERISTICS (Values are at T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	Forward Voltage Drop per Bridge Element	I _F = 1.0 A			1.1	V
I _R	DC Reverse Current	T _J = 25°C			3	μΑ
	at Rated DC Blocking Voltage	T _J = 125°C			500	
I ² t	Rating for Fusing (t < 8.3 ms)				5.1	A ² S
СЈ	Junction Capacitance	V _R = 4.0 V, f = 1.0 MHz		10		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DF005S1-DF10S1

TYPICAL PERFORMANCE CHARACTERISTICS

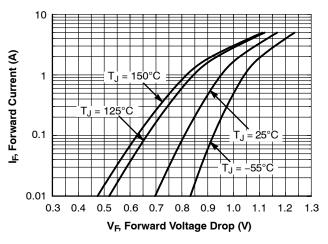


Figure 3. Typical Instantaneous Forward Characteristics

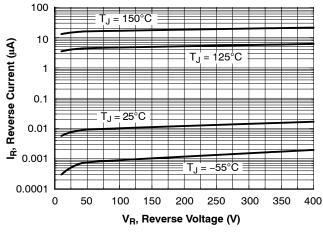


Figure 4. Typical Reverse Characteristics

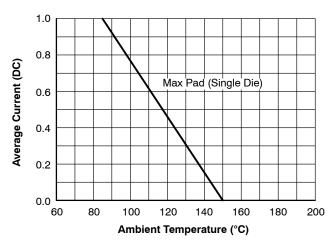


Figure 5. Maximum Average Current vs. Ambient Temperature

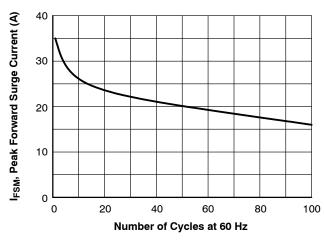


Figure 6. Peak Forward Surge Current vs.
Number of Cycles at 60 Hz

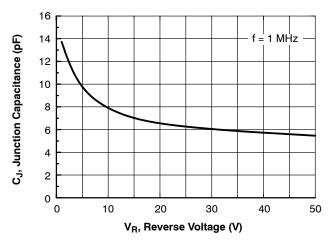


Figure 7. Typical Junction Capacitance

DF005S1-DF10S1

ORDERING INFORMATION

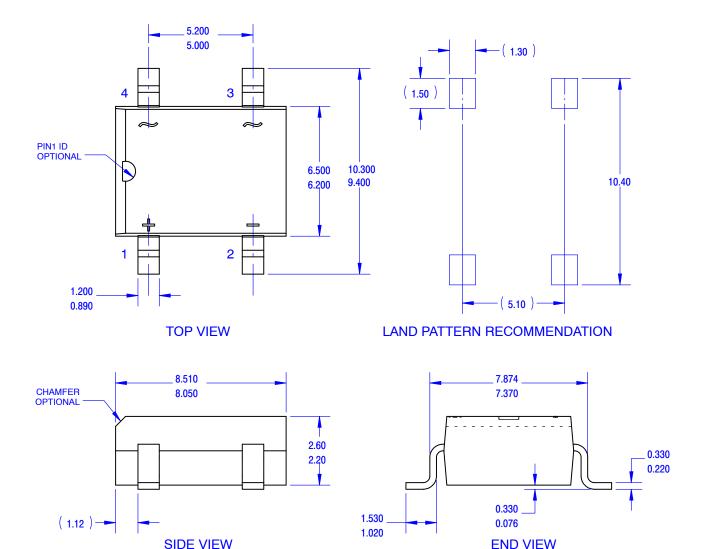
Part Number	Top Mark	Package	Shipping [†]			
DF005S1	DF005S1	PDIP4 GW	1500 / Tape & Reel			
DF01S1	DF01S1	(Pb-Free, Halide Free)				
DF02S1	DF02S1					
DF04S1	DF04S1					
DF06S1	DF06S1					
DF08S1	DF08S1					
DF10S1	DF10S1					

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



PDIP4 GW CASE 709AE ISSUE O

DATE 31 JUL 2016



NOTES:

- A. THIS PACKAGE DOES NOT CONFORM TO
- ANY REFERENCE STANDARD.
 B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

DOCUMENT NUMBER:	98AON13473G	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	PDIP4 GW		PAGE 1 OF 1			

onsemi and ONSemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.